

IN THE CLAIMS:

1-27. (canceled)

28. (Previously Presented) A semiconductor device including a CMOS circuit formed by an n-channel TFT and a p-channel TFT, wherein an active layer of the n-channel TFT is sandwiched by a first wiring line and a second wiring line through insulating layers, wherein the active layer includes a low concentration impurity region that is in contact with a channel formation region; and wherein the low concentration impurity region is formed to overlap the first wiring line and not to overlap the second wiring line.

29. (Currently Amended) A The semiconductor device according to claim 28, wherein the first wiring line is electrically connected with the second wiring line.

30. (Currently Amended) A semiconductor device including a CMOS circuit formed by an n-channel TFT and a p-channel TFT, wherein an active layer of the n-channel TFT is sandwiched by a first wiring line and a second wiring line through insulating layers; and wherein the second wiring line has a portion being a laminate of a first conductive layer and a third second conductive layer, and a portion being a laminate of the first conductive layer, a the second conductive layer and the a third conductive layer.

31. (Currently Amended) A The semiconductor device according to claim 30, wherein the third conductive layer has a lower resistance value than the first conductive layer and the second conductive layer.

32. (Currently Amended) A The semiconductor device according to claim 30, wherein at least one of the first wiring line and the second wiring line contains an element selected from the group consisting of tantalum (Ta), titanium (Ti), tungsten (W), molybdenum (Mo), and silicon (Si).

33. (Currently Amended) **A** The semiconductor device according to claim 30,  
wherein the third conductive layer mainly contains one of aluminum (Al) and copper (Cu).

34. (Previously Presented) A semiconductor device having a pixel matrix circuit  
that includes a pixel TFT and a storage capacitor formed by an n-channel TFT,

wherein the pixel TFT has a structure that an active layer is sandwiched by a first  
wiring line and a second wiring line through insulating layers,

wherein the active layer includes a low concentration impurity region that is in  
contact with a channel formation region; and

wherein the low concentration impurity region is formed to overlap the first wiring  
line and not to overlap the second wiring line.

35. (Currently Amended) **A** The semiconductor device according to claim 34,  
wherein the first wiring line is kept at one of a ground electric potential and a source power  
supply electric potential.

36. (Currently Amended) **A** The semiconductor device according to claim 34,  
wherein the first wiring line is kept at a floating electric potential.

37. (Previously Presented) A semiconductor device having a pixel matrix circuit  
that includes a pixel TFT and a storage capacitor formed by an n-channel TFT,

wherein the pixel TFT has a structure that an active layer is sandwiched by a first  
wiring line and a second wiring line through insulating layers, and

wherein the second wiring line has a portion being a laminate of a first conductive  
layer and a third second conductive layer, and a portion being a laminate of the first  
conductive layer, a the second conductive layer and the a third conductive layer.

38. (Currently Amended) **A** The semiconductor device according to claim 37,  
wherein the third conductive layer has a lower resistance value than the first conductive layer  
and the second conductive layer.

*13 12*  
 29. (Currently Amended) A The semiconductor device according to claim *37*,  
 wherein at least one of the first wiring line and the second wiring line contains an element  
 selected from the group consisting of tantalum (Ta), titanium (Ti), tungsten (W),  
 molybdenum (Mo), and silicon (Si).

*13 10*  
 30. (Currently Amended) A The semiconductor device according to claim *37*,  
 wherein the third conductive layer mainly contains one of aluminum (Al) and copper (Cu).

*14*  
 31. (Currently Amended) A semiconductor device having a pixel matrix circuit  
 and a driver circuit that are formed on a same substrate,

wherein each of a pixel TFT included in the pixel matrix circuit and an n-channel TFT  
 included in the driver circuit has a structure that each of including an active layers is layer  
sandwiched by each of a first wiring lines line and each of a second wiring lines line through  
each of insulating layers; and

wherein each of the active layers includes a low concentration impurity region that is  
in contact with each of channel formation regions;

wherein each of the low concentration impurity regions is formed to overlap each of  
the first wiring lines and not to overlap each of the second wiring lines;

wherein at least one of the second wiring lines has a portion being a laminate of a first  
conductive layer and a second conductive layer, and a portion being a laminate of the first  
conductive layer, the second conductive layer and a third conductive layer; and

wherein the first wiring line of the pixel TFT is kept at one of a fixed electric potential  
 and a floating electric potential, and the first wiring line of the n-channel TFT included in the  
 driver circuit is kept at the same level of electric potential as the second wiring line of the n-  
 channel TFT included in the driver circuit.

*42-44.* (Cancelled)

*15 14*  
 45. (Currently Amended) A The semiconductor device according to claim *41*,  
 wherein each at least one of the first wiring line or each of and the second wiring line

contains an element selected from the group consisting of tantalum (Ta), titanium (Ti), tungsten (W), molybdenum (Mo), and silicon (Si).

46. (Canceled)

16  
47. (Currently amended) A The semiconductor device according to any one of claims 28 to 43 41 and 45, wherein the semiconductor device is one of an active matrix liquid crystal display and an active matrix EL display.

17  
48. (Currently Amended) A The semiconductor device according to any one of claims 28 to 43 41 OR 45, wherein the semiconductor device is one selected from the group consisting of a video camera, a digital camera, a projector, a projection TV, a goggle type display, an automobile navigation system, a personal computer, and a portable information terminal.

49-54. (Canceled)

18  
55. (Currently Amended) A semiconductor device having a pixel matrix circuit and a driver circuit that are formed on a same substrate,

wherein each of a pixel TFT included in the pixel matrix circuit and an n-channel TFT included in the driver circuit has a structure that each of including an active layers is layer sandwiched by each of a first wiring lines line and each of a second wiring lines line through each of insulating layers;

wherein each of the active layers includes a low concentration impurity region that is in contact with each of channel formation regions;

wherein each of the low concentration impurity regions is formed to overlap each of the first wiring lines and not to overlap each of the second wiring lines; and

wherein the first wiring line of the pixel TFT is kept at one of a fixed electric potential and a floating electric potential, and the first wiring line of the n-channel TFT included in the driver circuit is kept at the same level of electric potential as the second wiring line of the n-channel TFT included in the driver circuit.

**19** **18**  
**56.** (Currently Amended) **A** The semiconductor device according to claim **55**, the semiconductor device is one of an active matrix liquid crystal display and an active matrix EL display.

**20** **18**  
**57.** (Currently Amended) **A** The semiconductor device according to claim **55**, the semiconductor device is one selected from the group consisting of a video camera, a digital camera, a projector, a projection TV, a goggle type display, an automobile navigation system, a personal computer, and a portable information terminal.

**21** **18**  
**58.** (Currently Amended) A semiconductor device having a pixel matrix circuit and a driver circuit that are formed on a same substrate,

wherein each of a pixel TFT included in the pixel matrix circuit and an n-channel TFT included in the driver circuit has a structure that ~~each of~~ including an active layers is layer sandwiched by each of a first wiring lines line and ~~each of~~ a second wiring lines line through ~~each of~~ insulating layers;

wherein at least one of the second wiring lines has a portion being a laminate of a first conductive layer and a ~~third~~ second conductive layer, and a portion being a laminate of the first conductive layer, a the second conductive layer and the a third conductive layer, and

wherein the first wiring line of the pixel TFT is kept at one of a fixed electric potential and a floating electric potential, and the first wiring line of the n-channel TFT included in the driver circuit is kept at the same level of electric potential as the second wiring line of the n-channel TFT included in the driver circuit.

**22** **21**  
**59.** (Currently Amended) **A** The semiconductor device according to claim **58**, wherein the third conductive layer has a lower resistance value than the first conductive layer and the second conductive layer.

**23** **21**  
**60.** (Currently Amended) **A** The semiconductor device according to claim **58**, wherein at least one of the first wiring line and the second wiring line contains an element

selected from the group consisting of tantalum (Ta), titanium (Ti), tungsten (W), molybdenum (Mo), and silicon (Si).

*24* 61. (Currently Amended) A The semiconductor device according to claim *58*, wherein the third conductive layer mainly contains one of aluminum (Al) and copper (Cu).

*25* 62. (Currently Amended) A The semiconductor device according to claim *58*, the semiconductor device is one of an active matrix liquid crystal display and an active matrix EL display.

*26* 63. (Currently Amended) A The semiconductor device according to claim *58*, the semiconductor device is one selected from the group consisting of a video camera, a digital camera, a projector, a projection TV, a goggle type display, an automobile navigation system, a personal computer, and a portable information terminal.

*27* 64. (New) The semiconductor device according to claim *28*, wherein at least one of the first wiring line and the second wiring line contains an element selected from the group consisting of tantalum (Ta), titanium (Ti), tungsten (W), molybdenum (Mo), and silicon (Si).

*28* 65. (New) The semiconductor device according to claim *30*, wherein the first wiring line is electrically connected with the second wiring line.

*29* 66. (New) The semiconductor device according to claim *34*, wherein at least one of the first wiring line and the second wiring line contains an element selected from the group consisting of tantalum (Ta), titanium (Ti), tungsten (W), molybdenum (Mo), and silicon (Si).

*30* 67. (New) The semiconductor device according to claim *37*, wherein the first wiring line is kept at one of a ground electric potential and a source power supply electric potential.

*31*  
68. (New) The semiconductor device according to claim *37*, wherein the first wiring line is kept at a floating electric potential.

*32*  
69. (New) The semiconductor device according to claim *41*, wherein the first wiring line of the n-channel TFT is electrically connected with the second wiring line of the n-channel TFT.

*33*  
70. (New) The semiconductor device according to claim *41*, wherein the third conductive layer has a lower resistance value than the first conductive layer and the second conductive layer.

*34*  
71. (New) The semiconductor device according to claim *41*, wherein the third conductive layer mainly contains one of aluminum (Al) and copper (Cu).

*35*  
72. (New) The semiconductor device according to claim *55*, wherein the first wiring line of the n-channel TFT is electrically connected with the second wiring line of the n-channel TFT.

*36*  
73. (New) The semiconductor device according to claim *55*, wherein at least one of the each of the first wiring line and the second wiring line contains an element selected from the group consisting of tantalum (Ta), titanium (Ti), tungsten (W), molybdenum (Mo), and silicon (Si).

*37*  
74. (New) The semiconductor device according to claim *58*, wherein the first wiring line of the n-channel TFT is electrically connected with the second wiring line of the n-channel TFT.